Ordering number : EN8205A

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

CPH5517 — PNP/NPN Epitaxial Planar Silicon Transistors High-Current Switching Applications

Applications

- relay drivers, lamp drivers, motor drivers

Features

- Composite type with a PNP/NPN transistor contained in package, facilitating high-density mounting
- The CPH5517 consists of two chips which are equivalent to the CPH3116 and the CPH3216, respectively
- Ultrasmall package permitting applied sets to be small and slime (mounting height : 0.9mm)

Specifications ( ): PNP

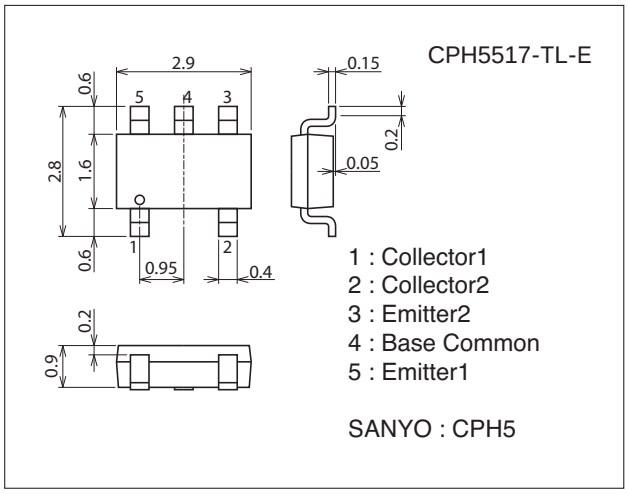
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		(−50)60	V
Collector-to-Emitter Voltage	V_{CEO}		(−)50	V
Emitter-to-Base Voltage	V_{EBO}		(−)5	V
Collector Current	I_C		(−)1.0	A
Collector Current (Pulse)	I_{CP}		(−)3	A
Base Current	I_B		(−)200	mA
Collector Dissipation	P_C	Mounted on a ceramic board (600mm^2×0.8mm) 1unit	0.9	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Package Dimensions

unit : mm (typ)

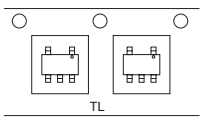
7017A-008



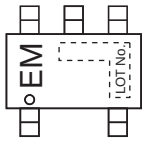
Product & Package Information

- Package : CPH5
- JEITA, JEDEC : SC-74A, SOT-25
- Minimum Packing Quantity : 3,000 pcs./reel

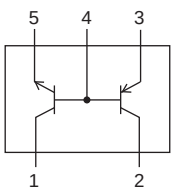
Packing Type : TL



Marking



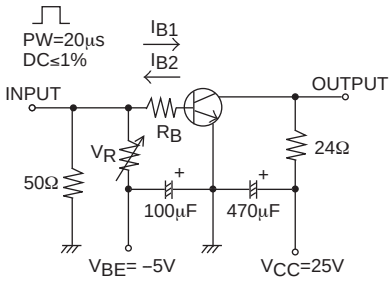
Electrical Connection



Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=(−)40V, I_E=0A			(−)0.1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=(−)4V, I_C=0A			(−)0.1	μA
DC Current Gain	h_{FE}	V_{CE}=(−)2V, I_C=(−)100mA	200		560	
Gain-Bandwidth Product	f_T	V_{CE}=(−)10V, I_C=(−)300mA		420		MHz
Output Capacitance	Cob	V_{CB}=(−)10V, f=1MHz		(9)6		pF
Collector-to-Emitter Saturation Voltage	V_{CE}(sat)	I_C=(−)500mA, I_B=(−)10mA		(−280)	(−430)	mV
				130	190	mV
		I_C=(−)300mA, I_B=(−)6mA		(−145)	(−220)	mV
				90	135	mV
Base-to-Emitter Saturation Voltage	V_{BE}(sat)	I_C=(−)500mA, I_B=(−)10mA		(−)0.81	(−)1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=(−)10μA, I_E=0A	(−50)60			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=(−)1mA, R_{BE}=∞	(−)50			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=(−)10μA, I_C=0A	(−)5			V
Turn-On Time	t_{on}	See specified Test Circuit.		(36)38		ns
Storage Time	t_{stg}			(173)332		ns
Fall Time	t_f			(28)40		ns

Switching Time Test Circuit

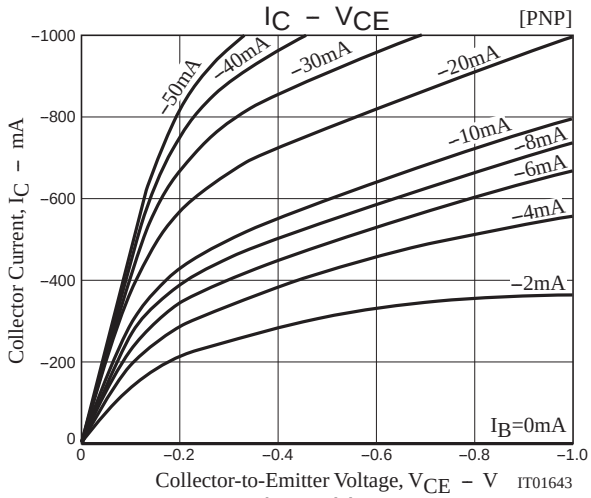


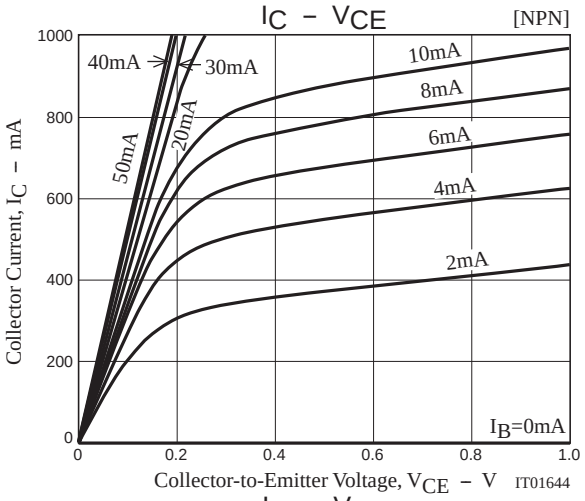
$20I_{B1}$= −$20I_{B2}$= I_C=500mA

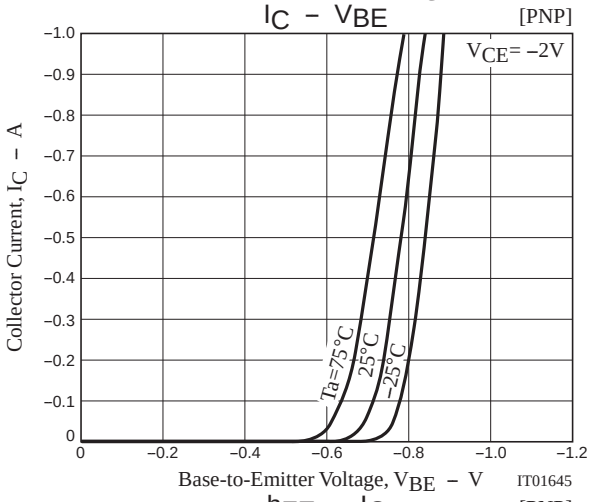
For PNP, the polarity is reversed.

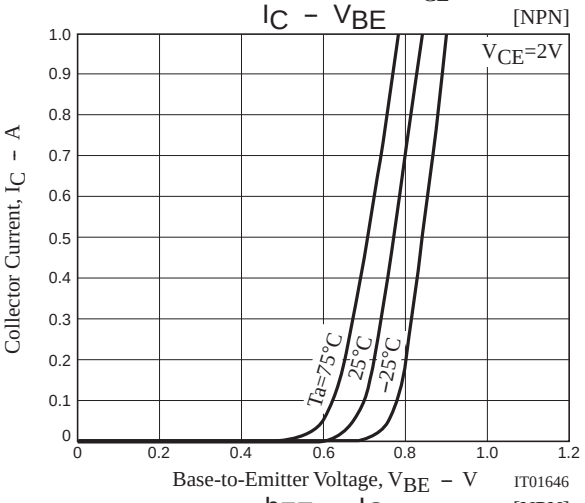
Ordering Information

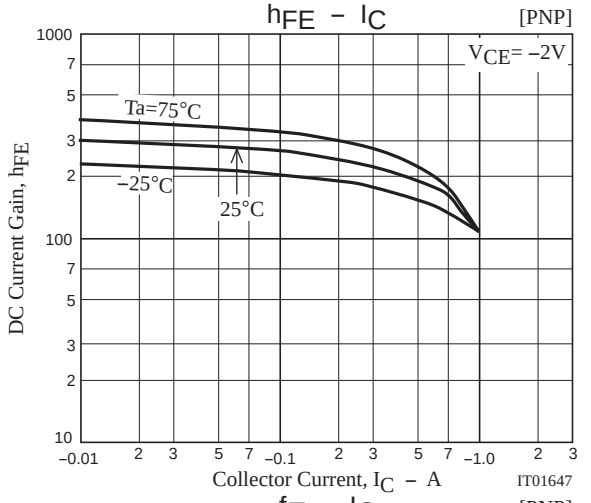
Device	Package	Shipping	memo
CPH5517-TL-E	CPH5	3,000pcs./reel	Pb Free

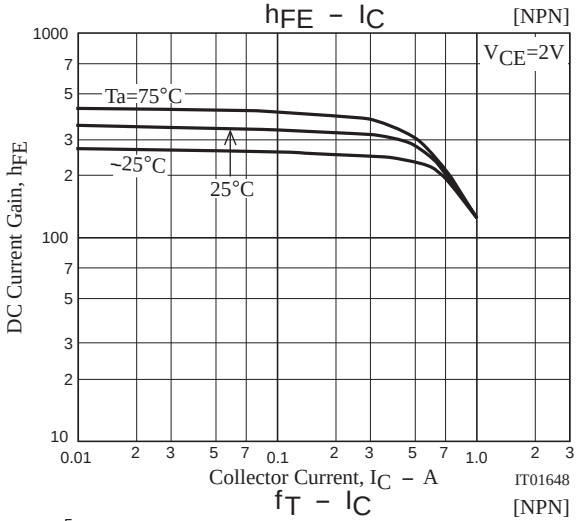

IC – VCE
[PNP]
Collector Current, IC – mA
Collector-to-Emitter Voltage, VCE – V
IT01643
–50mA
–40mA
–30mA
–20mA
–10mA
–8mA
–6mA
–4mA
–2mA
IB=0mA

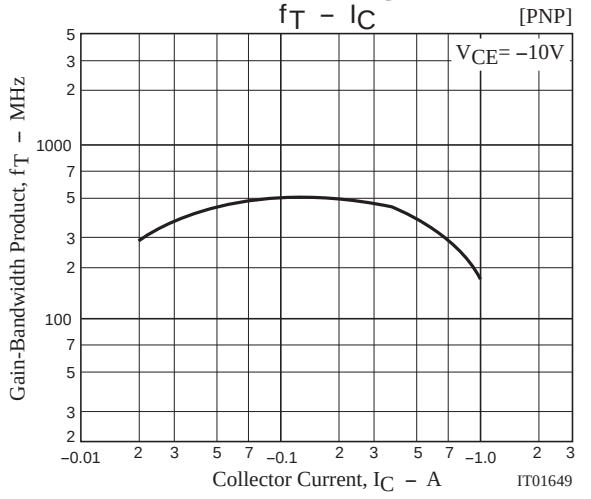

IC – VCE
[NPN]
Collector Current, IC – mA
Collector-to-Emitter Voltage, VCE – V
IT01644
40mA
30mA
50mA
20mA
10mA
8mA
6mA
4mA
2mA
IB=0mA

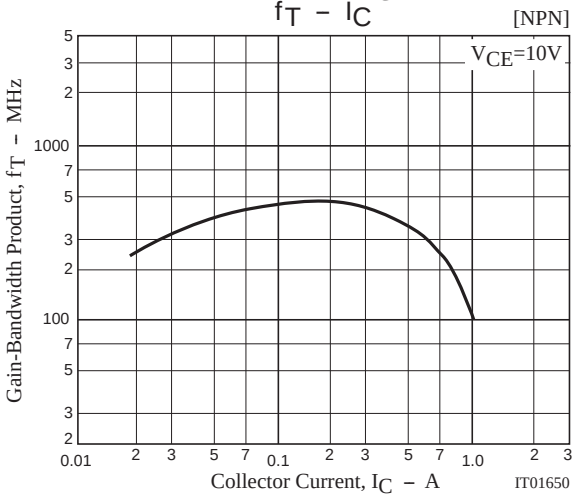

IC – VBE
[PNP]
VCE= –2V
Collector Current, IC – A
Base-to-Emitter Voltage, VBE – V
IT01645
Ta=75°C
25°C
–25°C

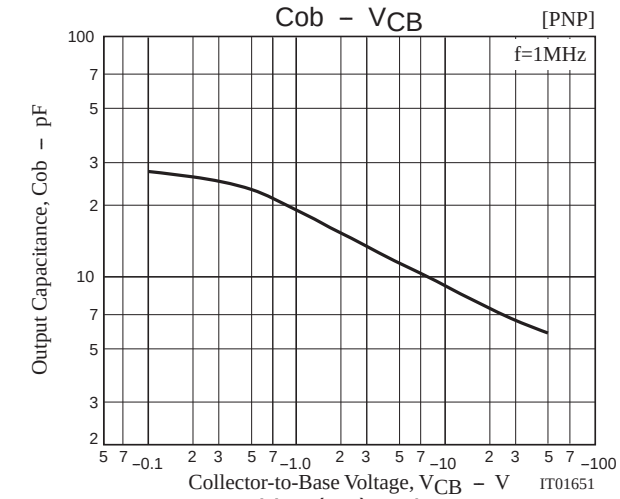

IC – VBE
[NPN]
VCE=2V
Collector Current, IC – A
Base-to-Emitter Voltage, VBE – V
IT01646
Ta=75°C
25°C
–25°C

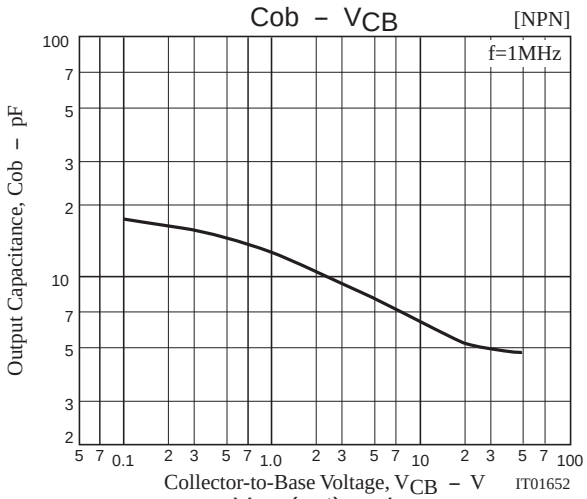

hFE – IC
[PNP]
VCE= –2V
DC Current Gain, hFE
Collector Current, IC – A
IT01647
Ta=75°C
–25°C
25°C

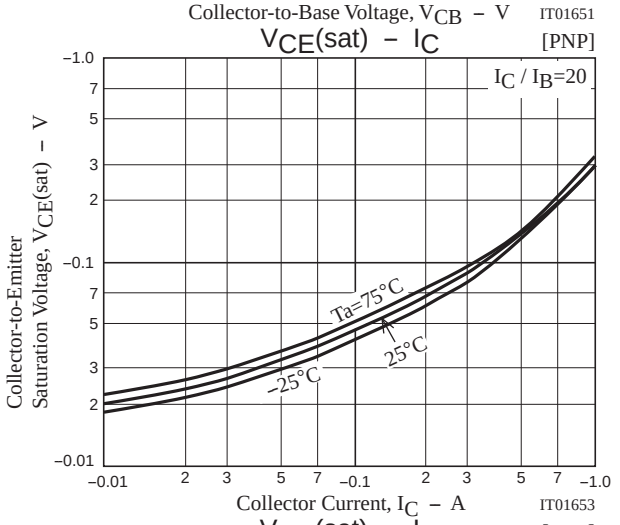

hFE – IC
[NPN]
VCE=2V
DC Current Gain, hFE
Collector Current, IC – A
IT01648
Ta=75°C
–25°C
25°C

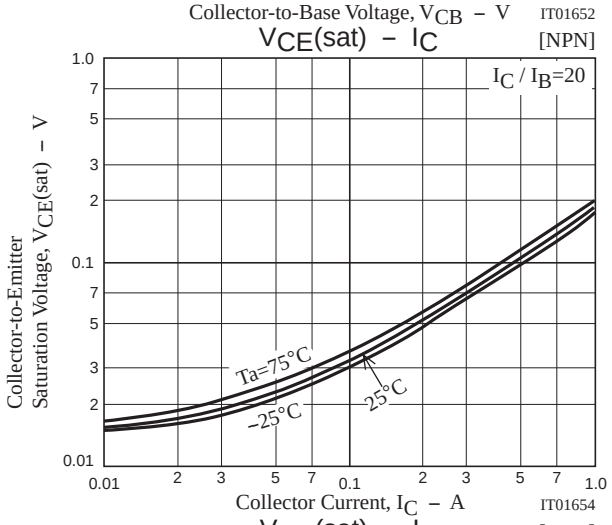

fT – IC
[PNP]
VCE= –10V
Gain-Bandwidth Product, fT – MHz
Collector Current, IC – A
IT01649

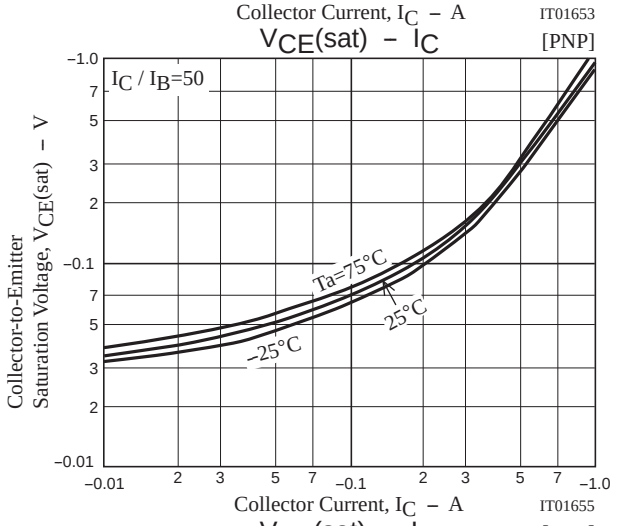

fT – IC
[NPN]
VCE=10V
Gain-Bandwidth Product, fT – MHz
Collector Current, IC – A
IT01650

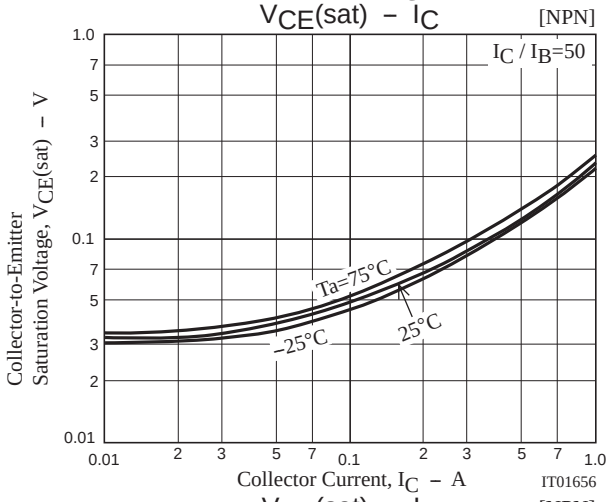

Cob – VCB
[PNP]
f=1MHz
Output Capacitance, Cob – pF
Collector-to-Base Voltage, VCB – V
IT01651

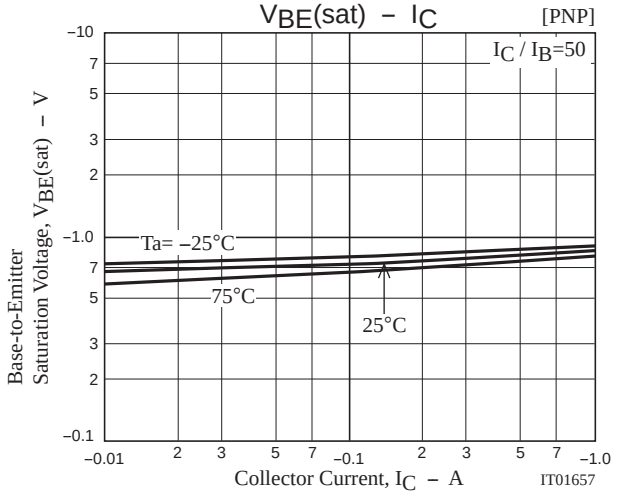

Cob – VCB
[NPN]
f=1MHz
Output Capacitance, Cob – pF
Collector-to-Base Voltage, VCB – V
IT01652

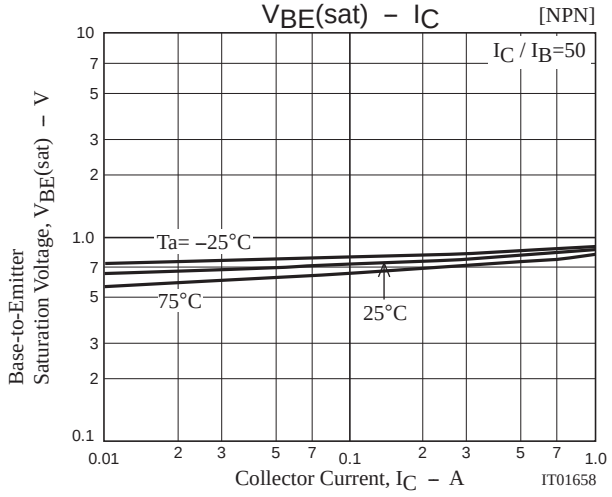

VCE(sat) – IC
[PNP]
IC / IB=20
Ta=75°C
25°C
–25°C
Collector-to-Emitter Saturation Voltage, VCE(sat) – V
Collector Current, IC – A
IT01653

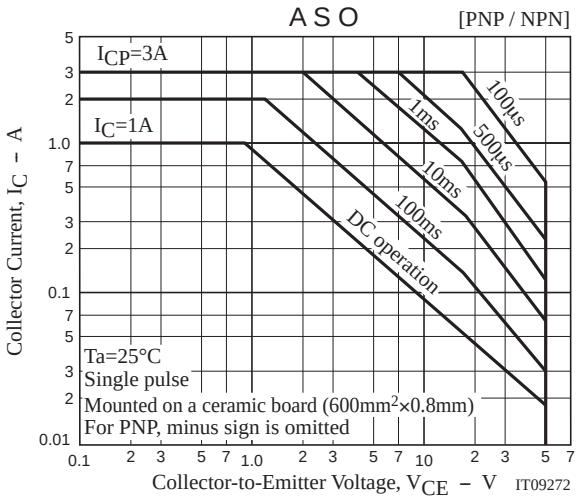

VCE(sat) – IC
[NPN]
IC / IB=20
Ta=75°C
25°C
–25°C
Collector-to-Emitter Saturation Voltage, VCE(sat) – V
Collector Current, IC – A
IT01654

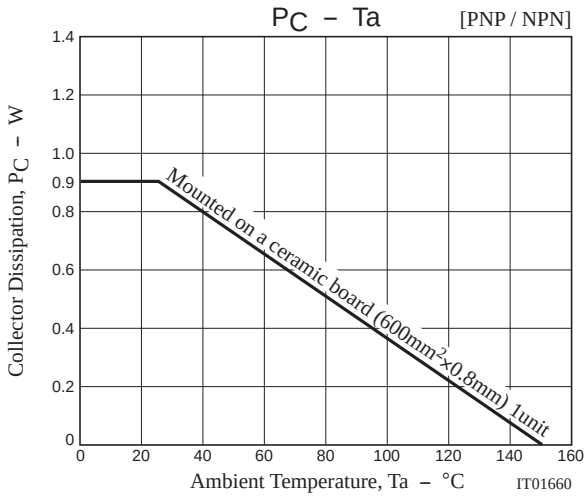

VCE(sat) – IC
[PNP]
IC / IB=50
Ta=75°C
25°C
–25°C
Collector-to-Emitter Saturation Voltage, VCE(sat) – V
Collector Current, IC – A
IT01655


VCE(sat) – IC
[NPN]
IC / IB=50
Ta=75°C
25°C
–25°C
Collector-to-Emitter Saturation Voltage, VCE(sat) – V
Collector Current, IC – A
IT01656


VBE(sat) – IC
[PNP]
IC / IB=50
Ta= –25°C
75°C
25°C
Base-to-Emitter Saturation Voltage, VBE(sat) – V
Collector Current, IC – A
IT01657


VBE(sat) – IC
[NPN]
IC / IB=50
Ta= –25°C
75°C
25°C
Base-to-Emitter Saturation Voltage, VBE(sat) – V
Collector Current, IC – A
IT01658


A S O
[PNP / NPN]
ICP=3A
IC=1A
100µs
1ms
500µs
10ms
100ms
DC operation
Ta=25°C
Single pulse
Mounted on a ceramic board (600mm2×0.8mm)
For PNP, minus sign is omitted
Collector Current, IC – A
Collector-to-Emitter Voltage, VCE – V
IT09272


PC – Ta
[PNP / NPN]
Mounted on a ceramic board (600mm2×0.8mm) 1unit
Collector Dissipation, PC – W
Ambient Temperature, Ta – °C
IT01660

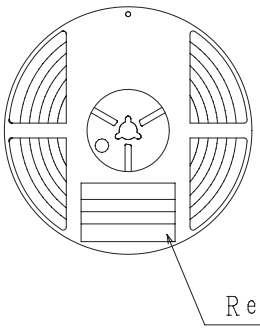
Embossed Taping Specification

CPH5517-TL-E

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
CPH5	CPH6	3,000	15,000	90,000	5 reels contained Dimensions:mm(external) 183×72×185	6 inner boxes contained Dimensions:mm(external) 440×195×210

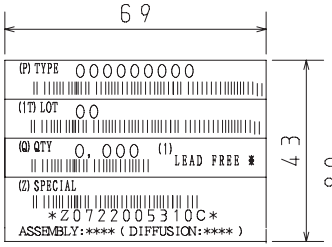
Packing method



Reel label

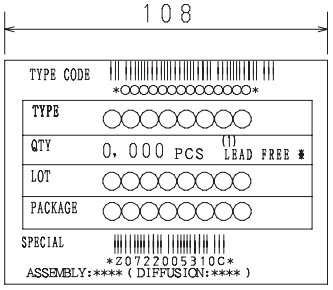
Reel label, Inner box label

(unit:mm)



Outer box label

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



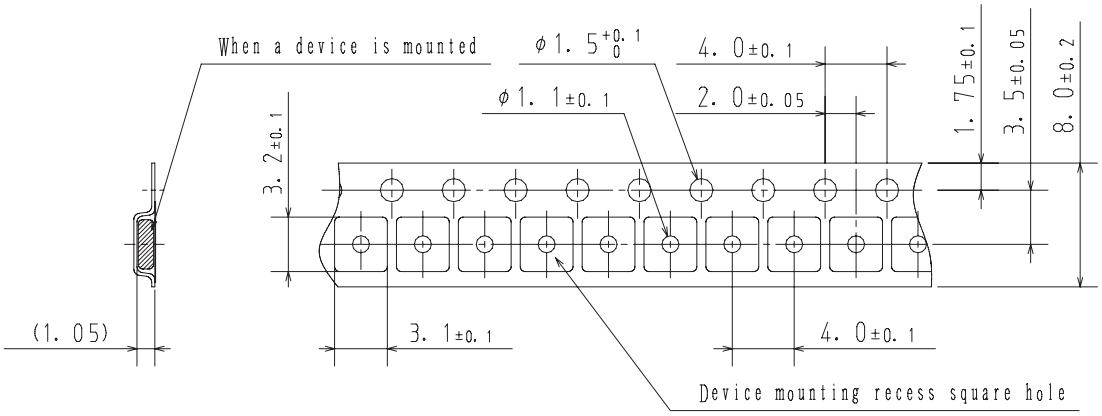
NOTE (1)

The LEAD FREE ※ description shows that the surface treatment of the terminal is lead free.

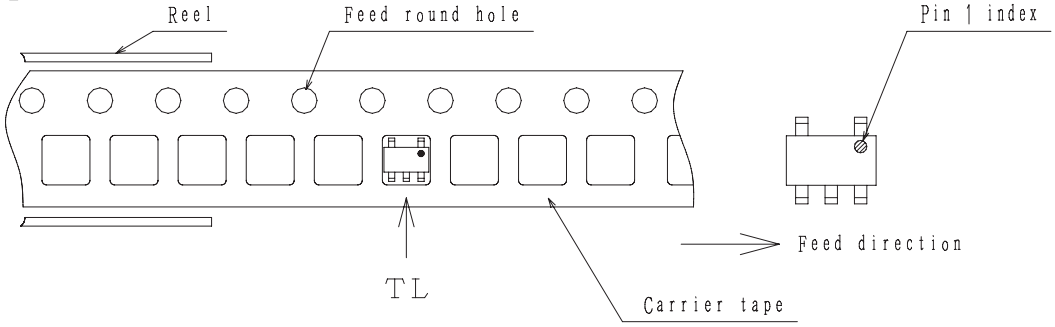
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



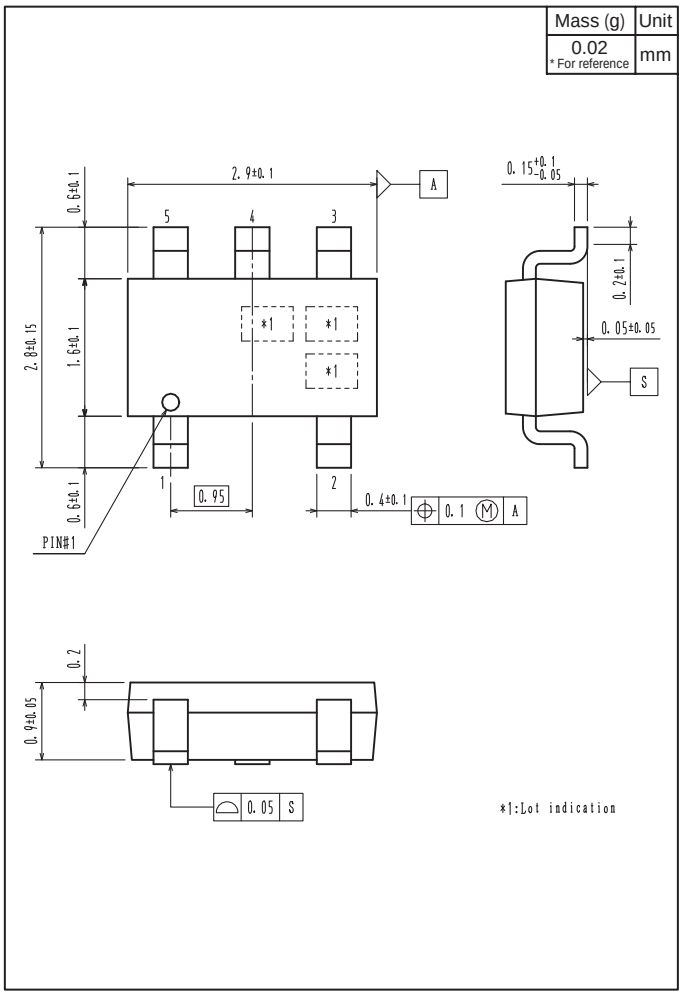
2-2. Device placement direction



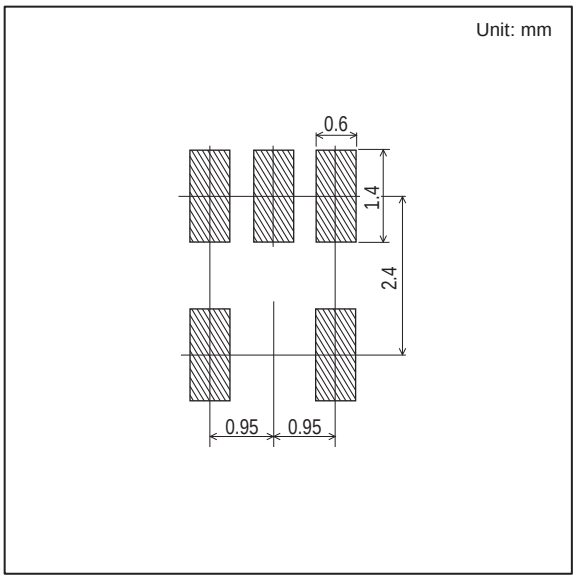
Those with pin 1 index on the feed hole side·····TL

Outline Drawing

CPH5517-TL-E



Land Pattern Example



This catalog provides information as of June, 2012. Specifications and information herein are subject to change without notice.

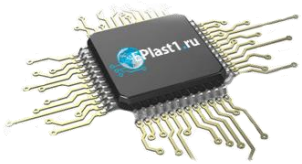
Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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Факс: 8 (812) 320-02-42
Электронная почта: org@eplast1.ru
Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.